



### DMTH47M2SPSWQ

#### 40V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

### **Product Summary**

BV <sub>DSS</sub>	RDS(ON) Max	l⊳Max Tc = +25°C
40V	7.5mΩ @ V <sub>GS</sub> = 10V	73A

## Features

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low RDS(ON) Minimizes Power Losses
- Wettable Flank for Improved Optical Inspection
- Fast Switching Speed
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
  Halogen and Antimony Free. "Green" Device (Note 3)
- Harogen and Antimony Free. "Green "Device (Note 3)
  The DMTH47M2SPSWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/guality/product-definitions/

## **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- High Frequency Switching
- Synchronous Rectification
- DC-DC Converters

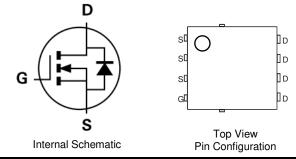




Bottom View

### **Mechanical Data**

- Package: PowerDI<sup>®</sup>5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)



## Ordering Information (Note 4)

Part Number	Package	Packing		
Fait Nulliber	Fackage	Qty.	Carrier	
DMTH47M2SPSWQ-13	PowerDI5060-8 (SWP) (Type UX)	2,500	Tape & Reel	

1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**

Notes:



)'' = Manufacturer's MarkingTH47M2SS = Product Type Marking CodeYYWW = Date Code MarkingYY = Year (ex: 21 = 2021)WW = Week (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated. DMTH47M2SPSWQ Document number: DS43527 Rev. 2 - 2

#### 1 of 7 www.diodes.com



## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	40	V	
Gate-Source Voltage	V <sub>GSS</sub>	±20	V	
Continuous Drain Current (Note 6), V <sub>GS</sub> = 10V	Tc = +25°C Tc = +100°C	D	73 51	А
Maximum Continuous Body Diode Forward Current (Note 6)		ls	73	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		Ідм	292	А
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	lsм	292	A	
Avalanche Current, L = 0.1mH	las	24.7	A	
Avalanche Energy, L = 0.1mH		Eas	30.5	mJ

## **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	TA = +25°C	PD	3.3	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	45	°C/W
Total Power Dissipation (Note 6)	Tc = +25°C	PD	68	W
Thermal Resistance, Junction to Case (Note 6)		Rejc	2.2	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

#### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	- <b>C</b> J		- 76		•		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40	_		V	VGS = 0V, ID = 250µA	
Zero Gate Voltage Drain Current	IDSS	_		1	μA	V <sub>DS</sub> = 32V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	lgss	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2		4	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	RDS(ON)		5.8	7.5	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A	
Diode Forward Voltage	V <sub>SD</sub>	_	0.9	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	897				
Output Capacitance	Coss		530		pF		
Reverse Transfer Capacitance	Crss		12.4	—			
Gate Resistance	Rg	_	2.07	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg		12.1				
Gate-Source Charge	Q <sub>gs</sub>	_	2.0	_	nC	$V_{DD} = 20V, I_D = 20A, V_{GS} = 10V$	
Gate-Drain Charge	Q <sub>gd</sub>		1.9				
Turn-On Delay Time	td(on)	_	5.4	_			
Turn-On Rise Time	t <sub>R</sub>	_	4.5	_		$\label{eq:VDD} \begin{split} V_{DD} &= 20V, \ V_{GS} = 10V, \\ R_g &= 3\Omega, \ I_D = 20A \end{split}$	
Turn-Off Delay Time	tD(OFF)	_	12.1		ns		
Turn-Off Fall Time	tF	_	5.6	—			
Body Diode Reverse Recovery Time	t <sub>RR</sub>		39.1		ns		
Body Diode Reverse Recovery Charge	QRR		53.3	—	nC	−I <sub>F</sub> = 20A, di/dt = 100A/μs	

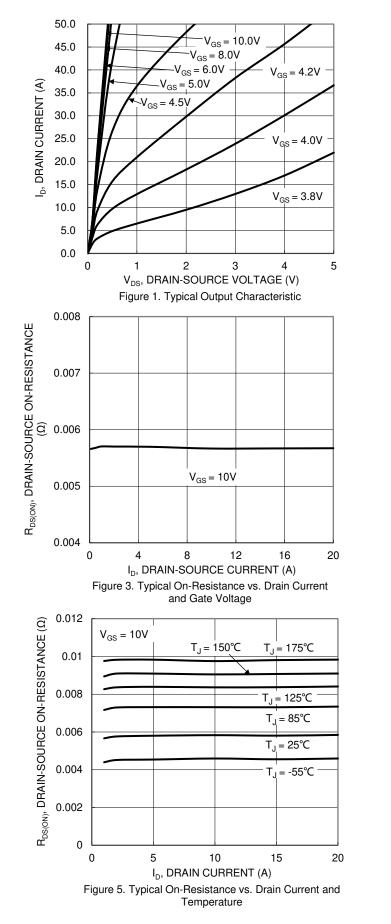
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1 inch square copper plate.

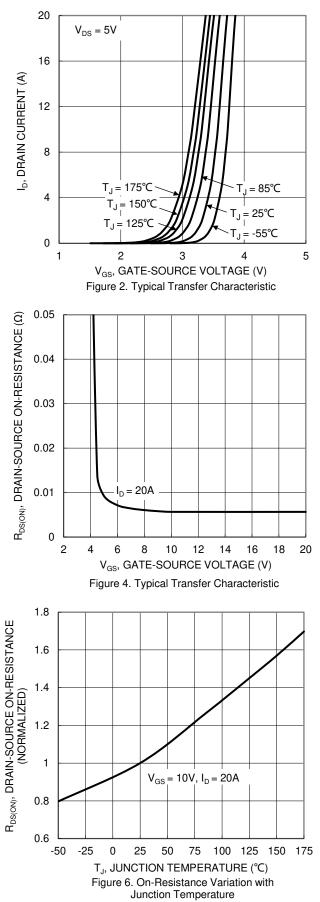
Thermal resistance from junction to soldering point (on the exposed drain pad).
 Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.



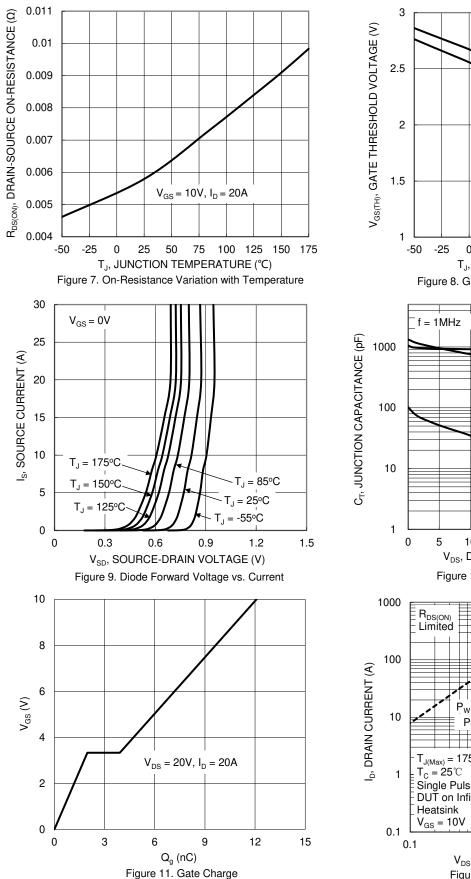
### DMTH47M2SPSWQ



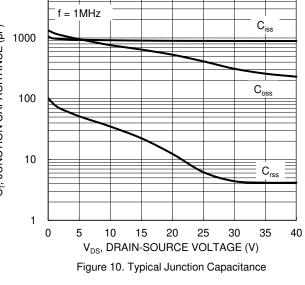


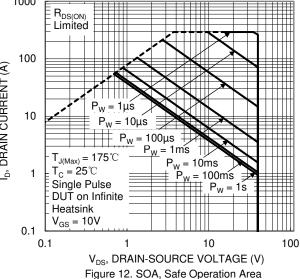


## DMTH47M2SPSWQ

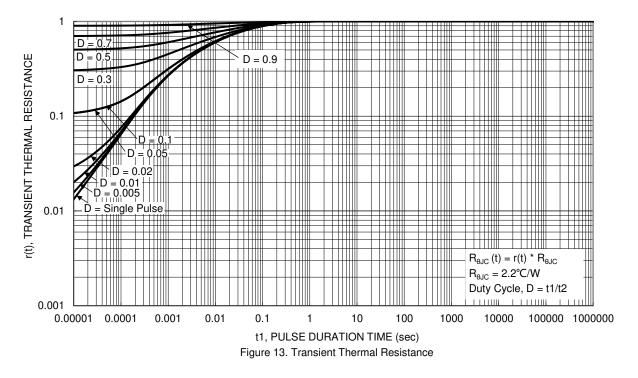


 $\begin{array}{c} \text{BD} \\ \text{2.5} \\ \text{2.5}$ 







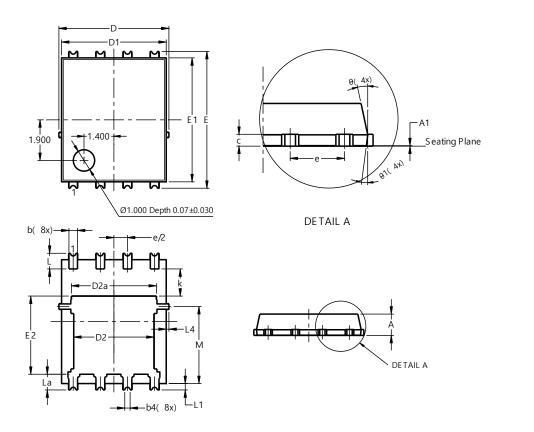




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (SWP) (Type UX)

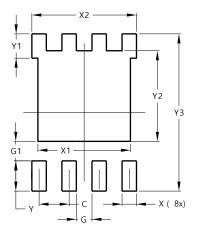


Pov	PowerDI5060-8 (SWP) (Type UX)				
Dim	Min	Тур			
Α	0.90	1.10	1.00		
A1	0	0.05			
b	0.30	0.50	0.41		
b2	0.20	0.35	0.25		
b4	C	).25REF	-		
С	0.230	0.330	0.277		
D	5	.15 BS(	0		
D1	4.70	5.10	4.90		
D2	3.56	3.96	3.76		
D2a	3.78	4.18	3.98		
E	6	6.40 BSC			
E1	5.60	6.00	5.80		
E2	3.46	3.86	3.66		
E2a	4.195	4.595	4.395		
е		.27BSC	)		
k	1.05				
L	0.635	0.835	0.735		
La	0.635	0.835	0.735		
L1	0.200	0.400	0.300		
L1a	0.050REF				
L4	0.025	0.225	0.125		
М	3.205	4.005	3.605		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All	Dimensi	ons in	mm		

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (SWP) (Type UX)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
Х	0.610		
X1	4.100		
X2	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



#### **IMPORTANT NOTICE**

1. DIODES INCORPORATED AND ITS SUBSIDIARIES ("DIODES") MAKE NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO ANY INFORMATION CONTAINED IN THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

2. The Information contained herein is for informational purpose only and is provided only to illustrate the operation of Diodes products described herein and application examples. Diodes does not assume any liability arising out of the application or use of this document or any product described herein. This document is intended for skilled and technically trained engineering customers and users who design with Diodes products. Diodes products may be used to facilitate safety-related applications; however, in all instances customers and users are responsible for (a) selecting the appropriate Diodes products for their applications, (b) evaluating the suitability of the Diodes products for their intended applications, (c) ensuring their applications, which incorporate Diodes products, comply the applicable legal and regulatory requirements as well as safety and functional-safety related standards, and (d) ensuring they design with appropriate safeguards (including testing, validation, quality control techniques, redundancy, malfunction prevention, and appropriate treatment for aging degradation) to minimize the risks associated with their applications.

3. Diodes assumes no liability for any application-related information, support, assistance or feedback that may be provided by Diodes from time to time. Any customer or user of this document or products described herein will assume all risks and liabilities associated with such use, and will hold Diodes and all companies whose products are represented herein or on Diodes' websites, harmless against all damages and liabilities.

4. Products described herein may be covered by one or more United States, international or foreign patents and pending patent applications. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks and trademark applications. Diodes does not convey any license under any of its intellectual property rights or the rights of any third parties (including third parties whose products and services may be described in this document or on Diodes' website) under this document.

5 products provided to Diodes' Standard Terms and Conditions of Sale Diodes are subject (https://www.diodes.com/about/company/terms-and-conditions/terms-and-conditions-of-sales/) or other applicable terms. This document does not alter or expand the applicable warranties provided by Diodes. Diodes does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.

6. Diodes products and technology may not be used for or incorporated into any products or systems whose manufacture, use or sale is prohibited under any applicable laws and regulations. Should customers or users use Diodes products in contravention of any applicable laws or regulations, or for any unintended or unauthorized application, customers and users will (a) be solely responsible for any damages, losses or penalties arising in connection therewith or as a result thereof, and (b) indemnify and hold Diodes and its representatives and agents harmless against any and all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim relating to any noncompliance with the applicable laws and regulations, as well as any unintended or unauthorized application.

7. While efforts have been made to ensure the information contained in this document is accurate, complete and current, it may contain technical inaccuracies, omissions and typographical errors. Diodes does not warrant that information contained in this document is error-free and Diodes is under no obligation to update or otherwise correct this information. Notwithstanding the foregoing, Diodes reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes.

8. Any unauthorized copying, modification, distribution, transmission, display or other use of this document (or any portion hereof) is prohibited. Diodes assumes no responsibility for any losses incurred by the customers or users or any third parties arising from any such unauthorized use.

Copyright © 2021 Diodes Incorporated

#### www.diodes.com